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O INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant(s): Sriram Satakopan et al.
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U.S. Patent Documents				
*Examiner Initial		Document Number	Date	Name
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)				
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	9	Kao et al., "Dual-Threshold Voltage Techniques for Low-Power Digital Circuits," IEEE Journal of Solid-State Circuits, Vol. 35, No. 7, July 2000, pages 1009-1018.		
	10	McPherson et al., "760 MHz G6 S/390 Microprocessor Exploiting Multiple Vt and Copper Interconnects," IEEE, ISSCC, Feb. 7, 2000, pages 96-97.		
	11	Miyake et al., "Design Methodology of High Performance Microprocessor using Ultra-Low Threshold Voltage CMOS," IEEE Custom Integrated Circuits Conference, May 6-9, 2001, pages 275-278.		
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.</p>				